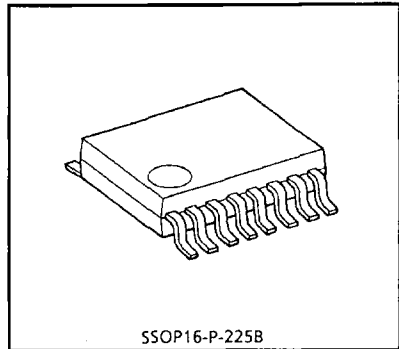


# IF AMP ICs AND I.Q. MODULATOR

## WIDE-BAND IF DETECTOR WITH BUILT-IN HIGH-SPEED MIX.

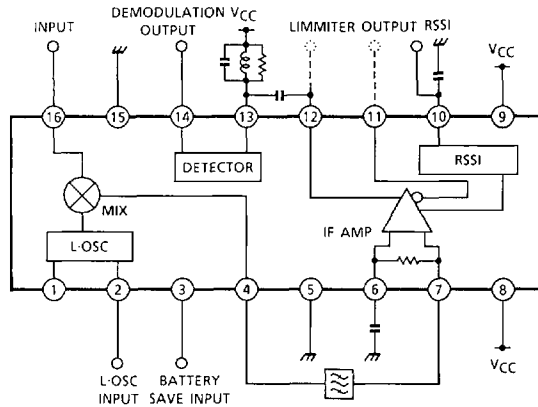
### FEATURES

- A wide-band IF detector integrated circuit capable of operating at 10.7MHz and designed for the high-speed bit rates used in mobile communication and other systems.
- Ideal for use as a receiver for digital mobile communication.
- MIX. operating frequency is in 40~300MHz range.
- Built-in frequency modulation detector (for 100kHz).
- High sensitivity
- High-speed RSSI response
- Low current consumption : 5.5mA (Typ.)
- Low-voltage operability (2.3~5.5V) makes it suitable for use in portable equipment.
- Miniature flat package : SSOP16 (0.65mm pitch)



SSOP16-P-225B  
Weight : 0.09g (Typ.)

### BLOCK DIAGRAM



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# IF AMP ICs AND I.Q. MODULATOR

PIN FUNCTION (The constants in the equivalent circuit diagrams indicate the design standards.)

PIN No.	PIN NAME	FUNCTION	EQUIVALENT INTERNAL CIRCUIT
1	OSC IN	Local oscillator input terminal. Can form an oscillator with an internal transistor and external crystal oscillator.	
2	OSC OUT	Can also operate as a mixer using the signal input externally from Pin 2.	
3	BS	Battery save terminal. Setting this terminal to low results in battery save state. Setting the terminal to high results in activate state.	
4	MIX OUT	MIX. output terminal. Externally connects filters. Output impedance is 330Ω (Typ.)	
5	GND1	Ground terminal	
6	DEC	Bias terminal for IF input terminals. Connects external capacitor. The value of the capacitor should be sufficiently large at 10.7MHz.	
7	IF IN	IF input terminal. Connected after the filters.	
8	VCC1	Power supply terminal (MIX. and part of IF)	
9	VCC2	Power supply terminal (part of IF and detector)	
10	RSSI	RSSI output terminal. Voltage output type.	
11	IFOUT1	IF output limiter terminal.	
12	IFOUT2	Output of pins 11 and 12 is opposite phase.	
13	QUAD	Phase input terminal for FM detector (frequency modulation detector).	



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# IF AMP ICs AND I.Q. MODULATOR

PIN No.	PIN NAME	FUNCTION	EQUIVALENT INTERNAL CIRCUIT
14	AF OUT	Modulation signal output terminal. Output impedance is $360\Omega$ (Typ.).	
15	GND2	Ground terminal	
16	MIX IN	MIX. input terminal. Double-balance MIX.	

## 1. Local Oscillator External Injection Method

Inject as shown in Fig.1, setting the injection level between  $95\text{dB}\mu\text{V}\sim 100\text{dB}\mu\text{V}$ . A built-in buffer AMP. minimizes leakage from the mixer.

Input from pin 1 is possible ; however, when the input frequency is high, the level at pin 2 may not be sufficient, causing a decrease in sensitivity.

In such a case, add resistor R51 and set the input signal so that the signal at pin 2 is adequate.

Connect as in Fig.3 to use internal transistor for oscillation.

R51 is the resistor that determines the oscillation current.

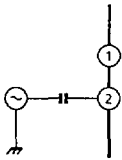


Fig.1

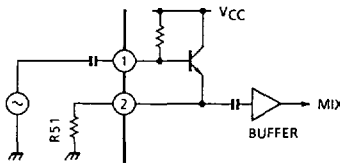


Fig.2

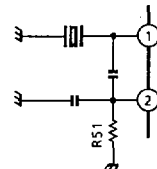


Fig.3

# IF AMP ICs AND I.Q. MODULATOR

## 2. Overtone Oscillation

Fig.4 shows the basic configuration of the local oscillation circuit using overtone oscillation.

The C51 and L1 tuning circuits prevent crystal fundamental oscillation.

Therefore, set C51 and L1 to inductive at the fundamental frequency and capacitive at the overtone frequency.

Since the level at pin 2 may decrease and the sensitivity may fall at high frequency as with external injection, adjust the oscillation level using R51.

The internal emitter follower circuit can oscillate up to 100MHz.

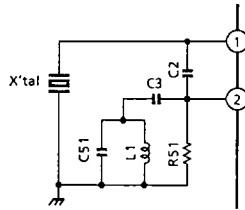


Fig.4

## 3. RSSI Function

A DC voltage corresponding to the input level of the IF IN terminal (Pin 7) is output to the RSSI terminal (Pin 10). While the linear range is about 70dB when  $V_{CC}=3V$ , the range can be expanded as in Fig.5. However, in such a case, note that the temperature characteristics of the RSSI output may alter due to a disparity between the temperature coefficient of the external resistor and the internal resistance of the IC.

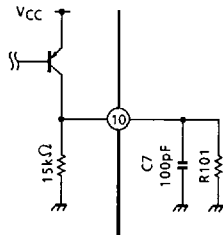
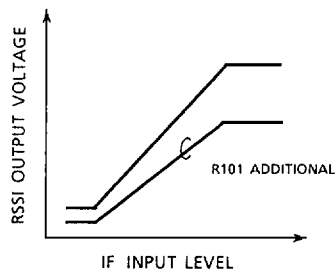


Fig.5



# IF AMP ICs AND I.Q. MODULATOR

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTICS	SYMBOL	RATINGS	UNIT
Power Supply Voltage	V <sub>CC</sub>	6	V
Power Dissipation	P <sub>D</sub>	240	mW
Operating Temperature	T <sub>opr</sub>	-35~85	°C
Storage Temperature	T <sub>stg</sub>	-55~150	°C

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTICS	SYMBOL	TEST CIR-CUIT	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Operating Voltage Range	V <sub>CC opr</sub>	—		2.3	3	5.5	V
Current Consumption	I <sub>CCQ</sub>	1	When local oscillation stopped	—	5.5	7.5	mA
Battery Save Current	I <sub>CCQ (BS)</sub>	1	BS = L state	—	0	10	μA
Mixer Operating Frequency	f <sub>opr</sub>	—		40	240	300	MHz
Mixer Conversion Gain	G <sub>VC</sub>	2	Excluding output filter attenuation	15	19	23	dB
Mixer Intercept Point	P <sub>IM</sub>	※	Input conversion value	—	95	—	dBμV
Mixer Equivalent Input Resistance	R <sub>IN (MIX)</sub>	—		—	1	—	kΩ
Mixer Equivalent Input Capacitance	C <sub>IN (MIX)</sub>	—		—	3	—	pF
Mixer 1dB Compression Level	DR (MIX)	※	Input conversion value	—	90	—	dBμV EMF
Mixer Output Resistance	R <sub>O (MIX)</sub>	—		—	330	—	Ω
Local Oscillator Operating Frequency	f (LO)	—		40	—	100	MHz
Recommended Local Input Level	LO	—		—	100	—	dBμV EMF
Local Equivalent Input Resistance	R <sub>IN (LO)</sub>	—		—	1	—	kΩ
Local Equivalent Input Capacitance	C <sub>IN (LO)</sub>	—		—	2.4	—	pF
IF Input Resistance Value	R <sub>IN (IF)</sub>	—		—	330	—	Ω
IF AMP Gain	G <sub>V (IF)</sub>	—		—	72	—	dB
IF Output Level	V <sub>O (IF)</sub>	—		400	500	600	mV <sub>p-p</sub>
RSSI Variation Width	V <sub>D (RSSI)</sub>	2		—	70	—	dB
RSSI Output Resistance	R (RSSI)	—		10.5	15	19.5	kΩ
RSSI Output Voltage	V (RSSI)	2	V <sub>IN</sub> = 70dBμV EMF	1.0	1.2	1.4	V

※ Tested in application circuit.

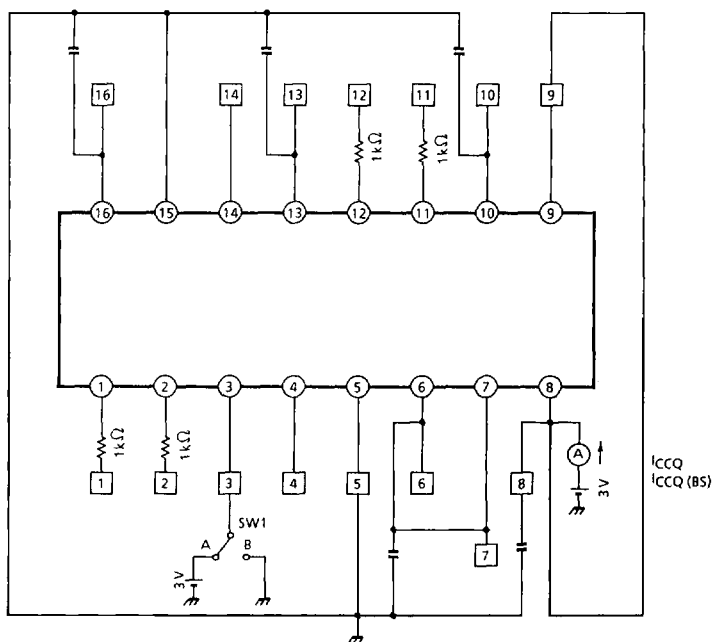
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# IF AMP ICs AND I.Q. MODULATOR

CHARACTERISTICS		SYMBOL	TEST CIRCUIT	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
BS Input Voltage	"H" Level	$V_{TH}(H)$	—	Active state	2	—	$V_{CC}$	V
	"L" Level	$V_{TH}(L)$	—	BS state	GND	—	0.2	
Demodulation Output Level		$V_O$	2	$DIV \pm 100kHz$	150	200	260	$mV_{rms}$
Demodulation Frequency		$f_{DET}$	—		—	100	—	kHz
12dB Sensitivity		12dB S/N	※		—	21	—	$dB_{\mu V}$ EMF
S/N Ratio		S/N	※		—	55	—	dB
AM Rejection Ratio		AMR	※		—	40	—	dB

※ Tested in application circuit.

TEST CIRCUIT 1



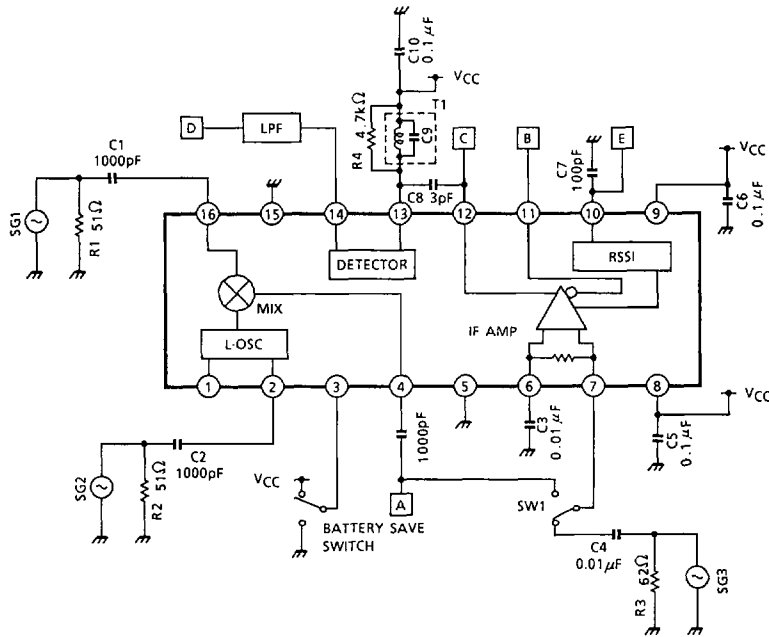
※ Capacitor without specified is  $0.01\mu F$   
 SW1 on A side when  $I_{CCQ}$  tested  
 SW1 on B side when  $I_{CCQ}(BS)$  tested

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# IF AMP ICs AND I.Q. MODULATOR

## TEST CIRCUIT 2



T1 : 4162-JPS-024  
(SUMIDA ELECTRIC CO., LTD.)  
F1 : FX-6506  
(MURATA MFG. CO., LTD.)

Test conditions for mixer conversion gain  $G_{VC}$

SG1 90.7MHz, 50dB $\mu$ V EMF

SG2 80.0MHz, 100dB $\mu$ V EMF

$G_{VC}$  = value at point **A** - 50dB

Test conditions for RSSI level output  $V$  (RSSI)

SG3 10.7MHz, 70dB $\mu$ V EMF

$V$  (RSSI) = voltage at point **E**

Test conditions for IF output level  $V_O$  (IF)

SG3 5MHz, 80dB $\mu$ V EMF

$V_O$  (IF) = peak output level at point **B** or point **C**

Test conditions for detect output  $V_O$

SG3 10.7MHz, modulation level  $\pm 100$ kHz, modulation frequency 1kHz, 80dB $\mu$ V EMF

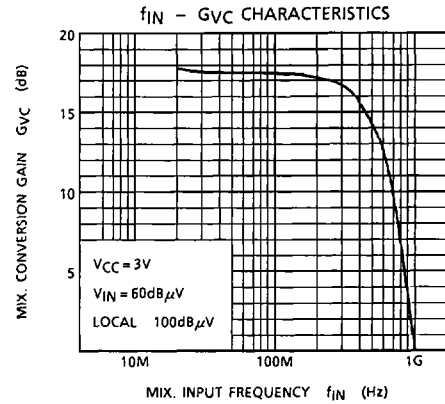
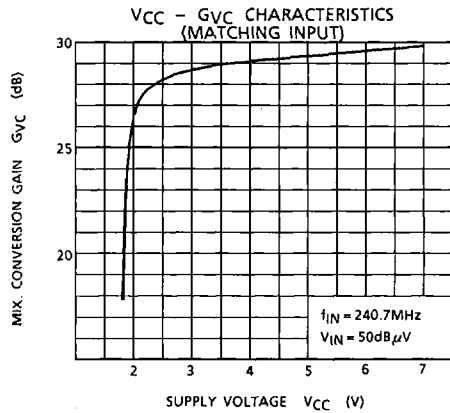
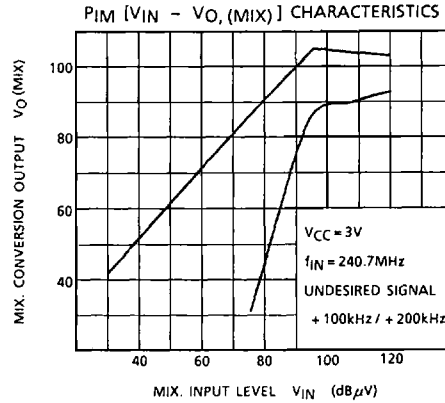
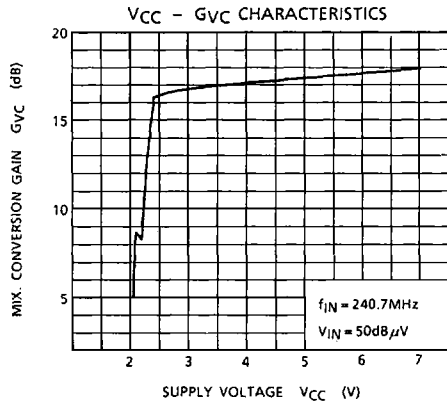
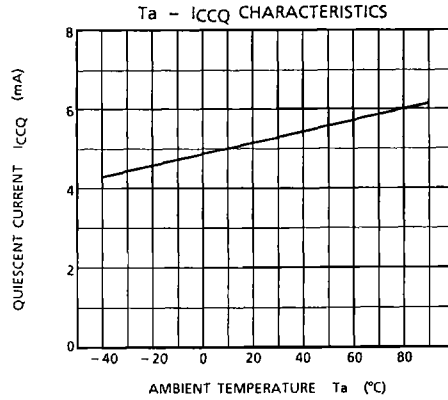
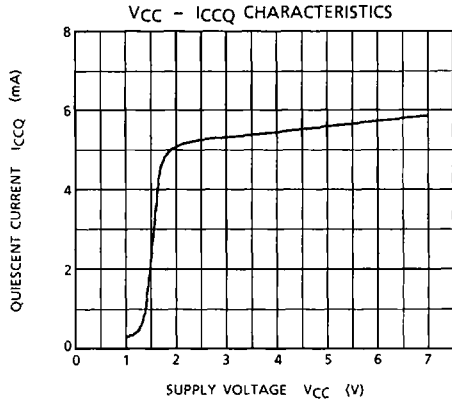
$V_O$  = voltage at point **D**

When  $V_{CC}$  = 3V, battery save switch on  $V_{CC}$  side, SW1 on SG3 side

(**A**) side only when  $G_{VC}$  tested)

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# IF AMP ICs AND I.Q. MODULATOR

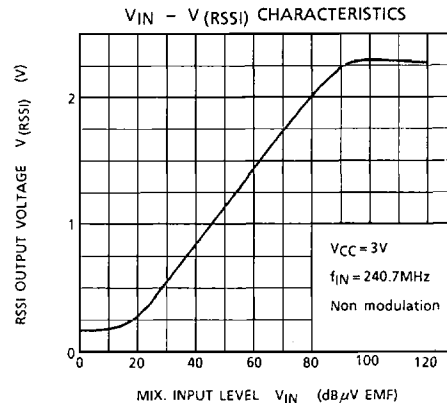
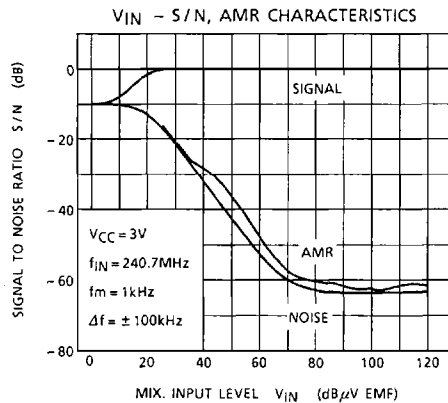
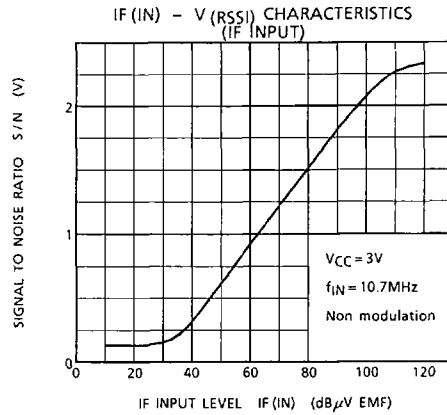
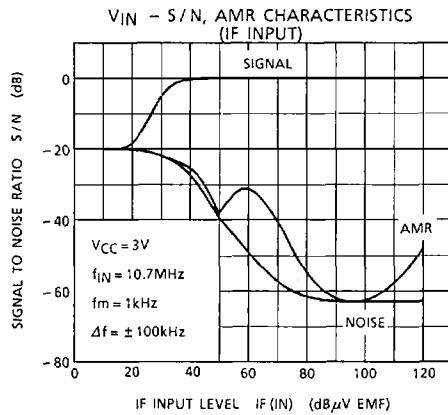
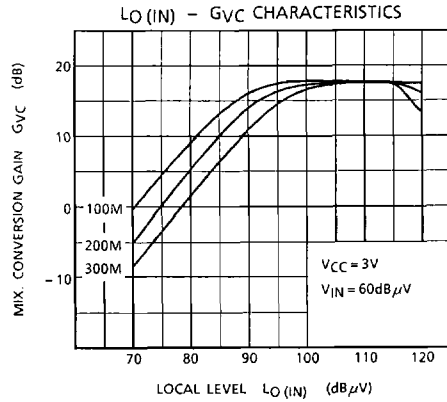
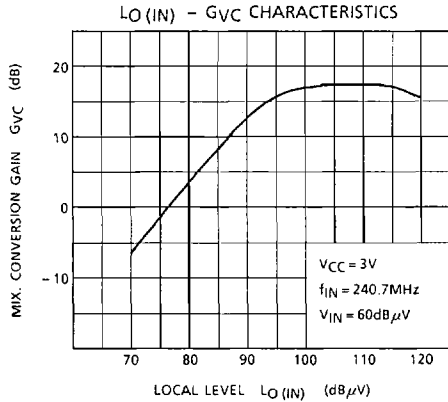


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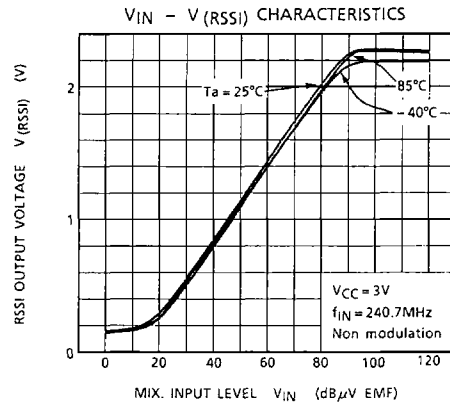
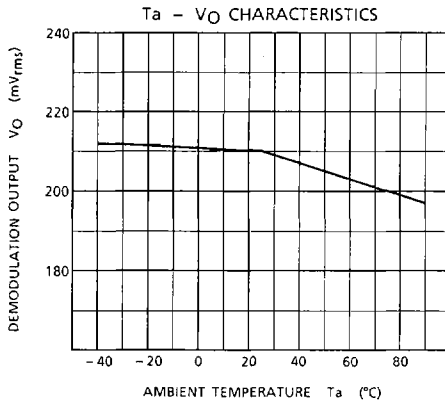
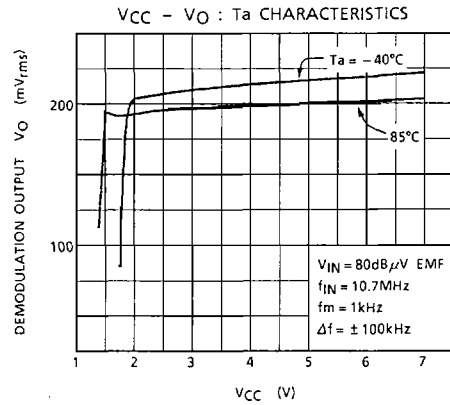
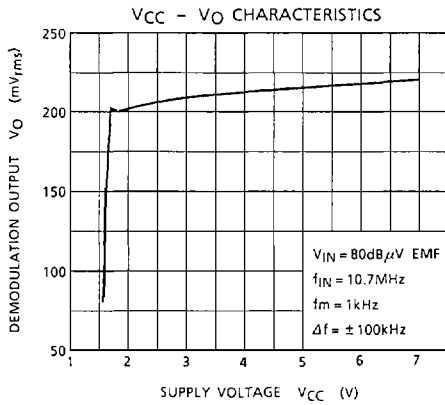
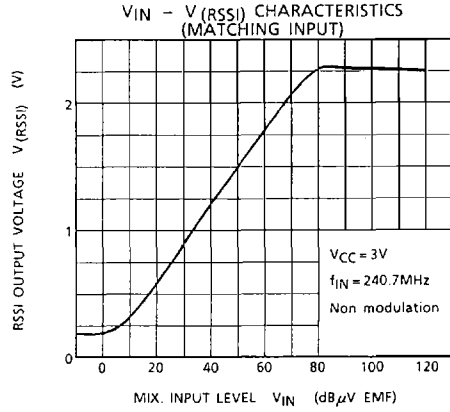
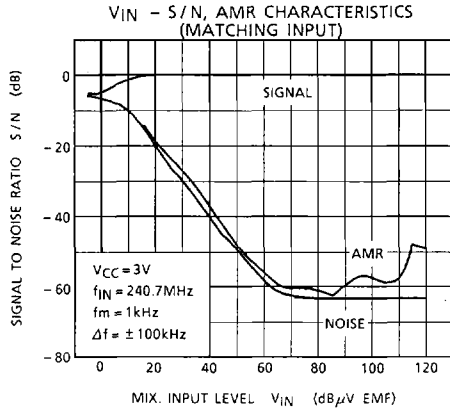


# IF AMP ICs AND I.Q. MODULATOR



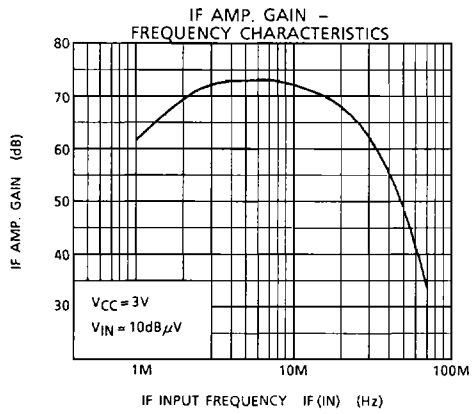
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# IF AMP ICs AND I.Q. MODULATOR



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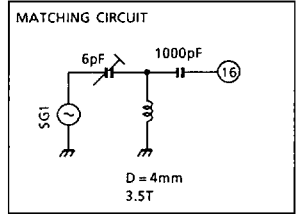
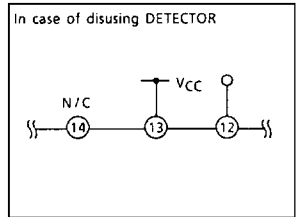
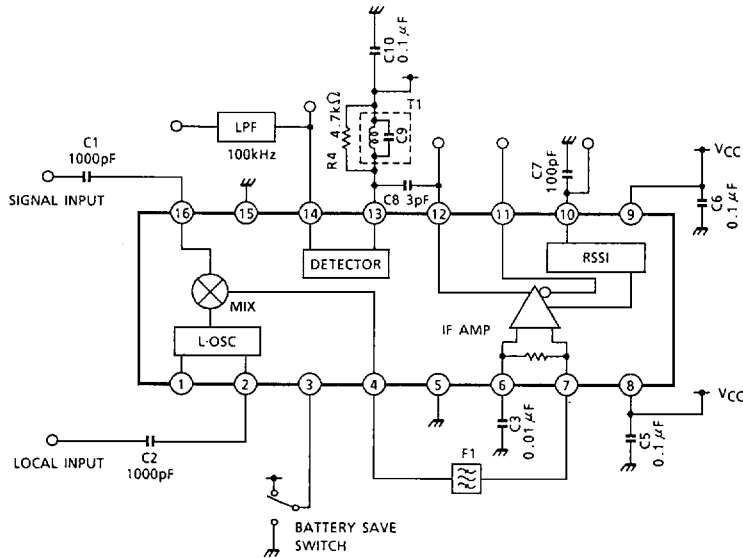
# IF AMP ICs AND I.Q. MODULATOR



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# IF AMP ICs AND I.Q. MODULATOR

## APPLICATION CIRCUIT



- T1 : 4162-JPS-024  
(SUMIDA ELECTRIC CO., LTD.)
- F1 : FX-6506  
(MURATA MFG. CO., LTD.)

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